



# CMOS Static RAM 1 Meg (64K x 16-Bit)

IDT71016S/NS

## Features

- ◆ 64K x 16 advanced high-speed CMOS Static RAM
- ◆ Equal access and cycle times
  - Commercial and Industrial: 12/15/20ns
- ◆ One Chip Select plus one Output Enable pin
- ◆ Bidirectional data inputs and outputs directly TTL-compatible
- ◆ Low power consumption via chip deselect
- ◆ Upper and Lower Byte Enable Pins
- ◆ Commercial and industrial product available in 44-pin Plastic SOJ package and 44-pin TSOP package

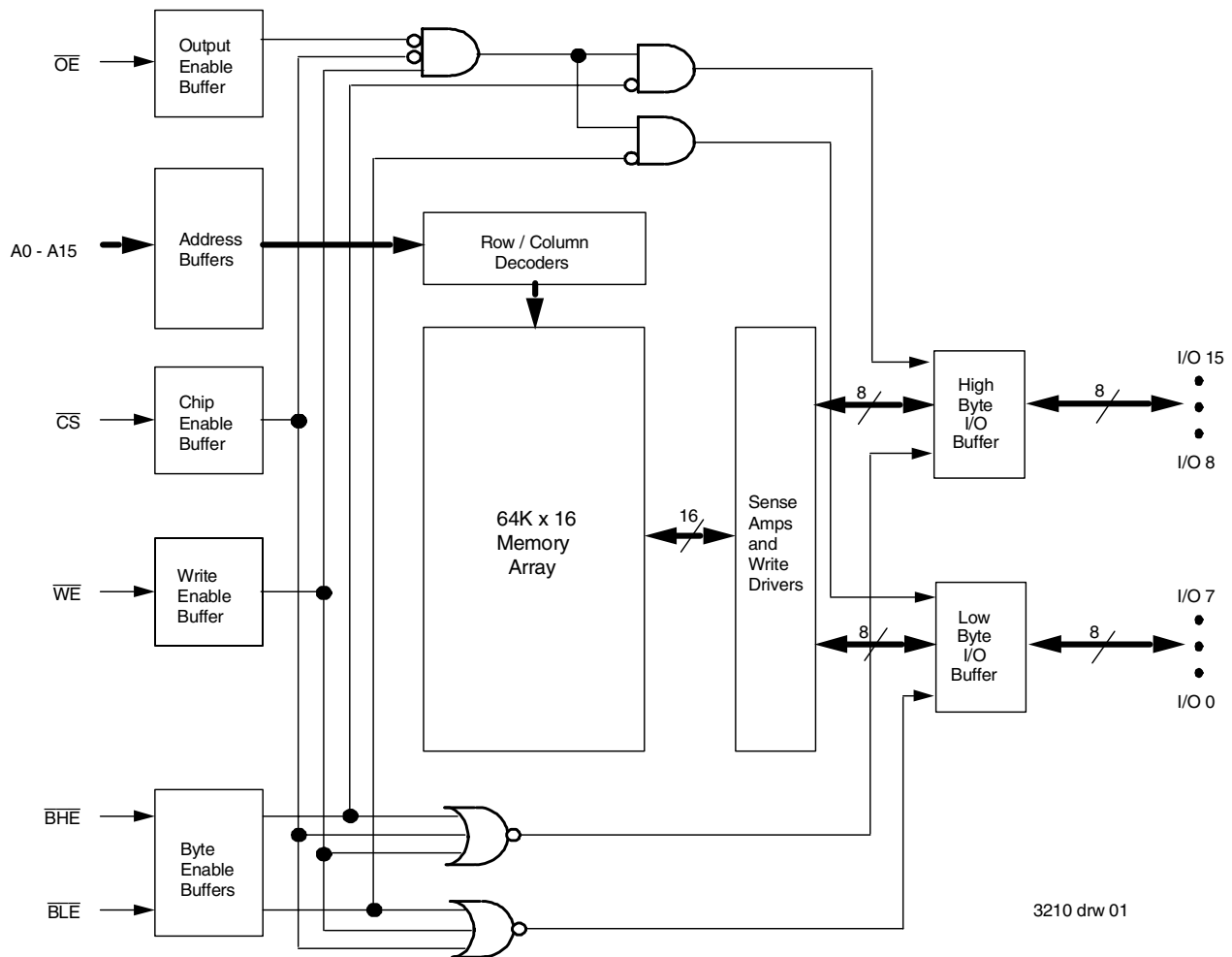
## Description

The IDT71016 is a 1,048,576-bit high-speed Static RAM organized as 64K x 16. It is fabricated using IDT's high-performance, high-reliability CMOS technology. This state-of-the-art technology, combined with innovative circuit design techniques, provides a cost-effective solution for high-speed memory needs.

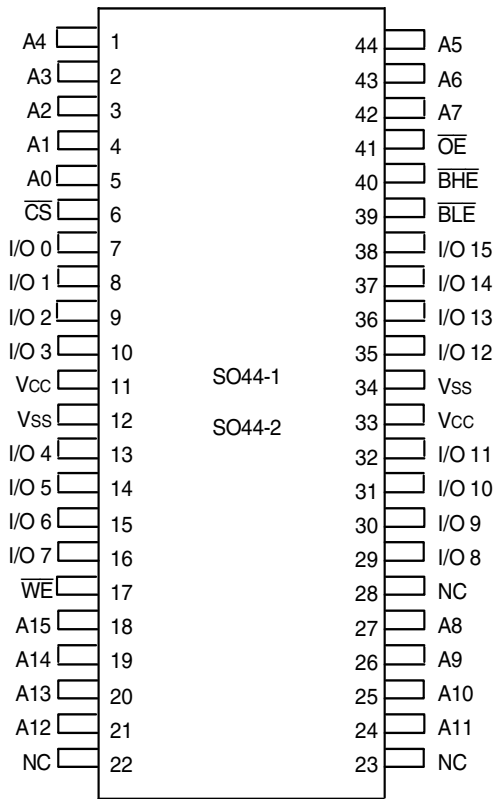
The IDT71016 has an output enable pin which operates as fast as 7ns, with address access times as fast as 12ns. All bidirectional inputs and outputs of the IDT71016 are TTL-compatible and operation is from a single 5V supply. Fully static asynchronous circuitry is used, requiring no clocks or refresh for operation.

The IDT71016 is packaged in a JEDEC standard 44-pin Plastic SOJ and 44-pin TSOP Type II.

## Functional Block Diagram



### Pin Configurations



3210 drw 02

SOJ/TSOP  
Top View

### Pin Descriptions

A0 - A15	Address Inputs	Input
$\overline{CS}$	Chip Select	Input
$\overline{WE}$	Write Enable	Input
$\overline{OE}$	Output Enable	Input
$\overline{BHE}$	High Byte Enable	Input
$\overline{BLE}$	Low Byte Enable	Input
I/O <sub>0</sub> - I/O <sub>15</sub>	Data Input/Output	I/O
V <sub>cc</sub>	5.0V Power	Pwr
V <sub>ss</sub>	Ground	Gnd

3210 tbl 01

### Truth Table <sup>(1)</sup>

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	$\overline{BLE}$	$\overline{BHE}$	I/O <sub>0</sub> - I/O <sub>7</sub>	I/O <sub>8</sub> - I/O <sub>15</sub>	Function
H	X	X	X	X	High-Z	High-Z	Deselected - Standby
L	L	H	L	H	DATAOUT	High-Z	Low Byte Read
L	L	H	H	L	High-Z	DATAOUT	High Byte Read
L	L	H	L	L	DATAOUT	DATAOUT	Word Read
L	X	L	L	L	DATAIN	DATAIN	Word Write
L	X	L	L	H	DATAIN	High-Z	Low Byte Write
L	X	L	H	L	High-Z	DATAIN	High Byte Write
L	H	H	X	X	High-Z	High-Z	Outputs Disabled
L	X	X	H	H	High-Z	High-Z	Outputs Disabled

**NOTE:**

1. H = V<sub>H</sub>, L = V<sub>L</sub>, X = Don't care.

3210 tbl 02

## Absolute Maximum Ratings<sup>(1)</sup>

Symbol	Rating	Value	Unit
V <sub>TERM</sub> <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
T <sub>A</sub>	Operating Temperature	0 to +70	°C
T <sub>BIAS</sub>	Temperature Under Bias	-55 to +125	°C
T <sub>STG</sub>	Storage Temperature	-55 to +125	°C
P <sub>T</sub>	Power Dissipation	1.25	W
I <sub>OUT</sub>	DC Output Current	50	mA

3210 tbl 03

### NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- V<sub>TERM</sub> must not exceed V<sub>CC</sub> + 0.5V.

## Recommended Operating Temperature and Supply Voltage

Grade	Temperature	GND	V <sub>CC</sub>
Commercial	0°C to +70°C	0V	5.0V ± 10%
Industrial	-40°C to +85°C	0V	5.0V ± 10%

3210 tbl 04

## Recommended DC Operating Conditions

Symbol	Parameter	Min.	Typ.	Max.	Unit
V <sub>CC</sub>	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
V <sub>IH</sub>	Input High Voltage	2.2	—	V <sub>DD</sub> + 0.5	V
V <sub>IL</sub>	Input Low Voltage	-0.5 <sup>(1)</sup>	—	0.8	V

### NOTE:

- V<sub>IL</sub> (min.) = -1.5V for pulse width less than t<sub>RC</sub>/2, once per cycle.

3210 tbl 05

## Capacitance

(T<sub>A</sub> = +25°C, f = 1.0MHz, SOJ/TSOP Package)

Symbol	Parameter <sup>(1)</sup>	Conditions	Max.	Unit
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = 3dV	6	pF
C <sub>I/O</sub>	I/O Capacitance	V <sub>OUT</sub> = 3dV	7	pF

### NOTE:

- This parameter is guaranteed by device characterization, but not production tested.

3210 tbl 06

## DC Electrical Characteristics

(V<sub>CC</sub> = 5.0V ± 10%, Commercial and Industrial Temperature Range)

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
I <sub>L</sub>	Input Leakage Current	V <sub>CC</sub> = Max., V <sub>IN</sub> = GND to V <sub>CC</sub>	—	5	μA
I <sub>LO</sub>	Output Leakage Current	V <sub>CC</sub> = Max., $\overline{CS}$ = V <sub>IH</sub> , V <sub>OUT</sub> = GND to V <sub>CC</sub>	—	5	μA
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = 8mA, V <sub>CC</sub> = Min.	—	0.4	V
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -4mA, V <sub>CC</sub> = Min.	2.4	—	V

3210 tbl 07

## DC Electrical Characteristics<sup>(1)</sup>

(V<sub>CC</sub> = 5.0V ± 10%, V<sub>LC</sub> = 0.2V, V<sub>HC</sub> = V<sub>CC</sub> - 0.2V)

Symbol	Parameter	71016S12		71016S15		71016S20		Unit
		Com'l.	Ind.	Com'l.	Ind.	Com'l.	Ind.	
I <sub>CC</sub>	Dynamic Operating Current $\overline{CS} \leq V_{IL}$ , Outputs Open, V <sub>CC</sub> = Max., f = f <sub>MAX</sub> <sup>(2)</sup>	210	210	180	180	170	170	mA
I <sub>SB</sub>	Standby Power Supply Current (TTL Level) $\overline{CS} \geq V_{IH}$ , Outputs Open, V <sub>CC</sub> = Max., F = f <sub>MAX</sub> <sup>(2)</sup>	60	60	50	50	45	45	mA
I <sub>SB1</sub>	Standby Power Supply Current (CMOS Level) $\overline{CS} \geq V_{HC}$ , Outputs Open, V <sub>CC</sub> = Max., f = 0 <sup>(2)</sup> V <sub>IN</sub> ≤ V <sub>LC</sub> or V <sub>IN</sub> ≥ V <sub>HC</sub>	10	10	10	10	10	10	mA

### NOTES:

- All values are maximum guaranteed values.
- f<sub>MAX</sub> = 1/t<sub>RC</sub> (all address inputs are cycling at f<sub>MAX</sub>); f = 0 means no address input lines are changing.

3210 tbl 08

## AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	1.5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
AC Test Load	See Figure 1, 2 and 3

3210 tbl 09

## AC Test Loads

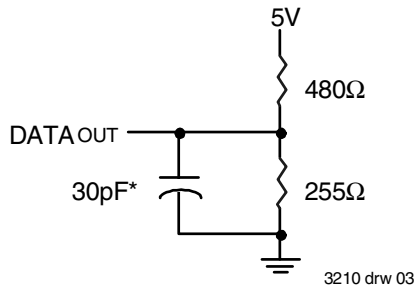


Figure 1. AC Test Load

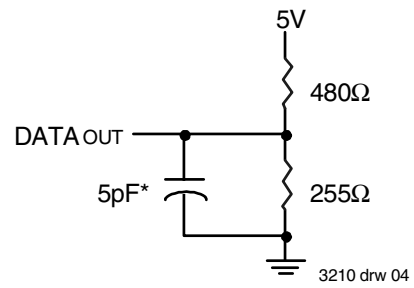


Figure 2. AC Test Load  
(for t<sub>CLZ</sub>, t<sub>OLZ</sub>, t<sub>CHZ</sub>, t<sub>OHZ</sub>, t<sub>OW</sub>, and t<sub>WHZ</sub>)

\*Including jig and scope capacitance.

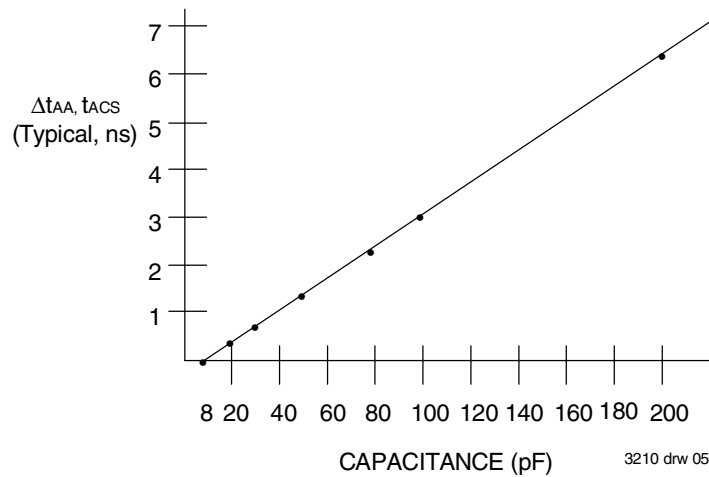


Figure 3. Output Capacitive Derating

AC Electrical Characteristics (VCC = 5.0V ± 10%, Commercial and Industrial Range)

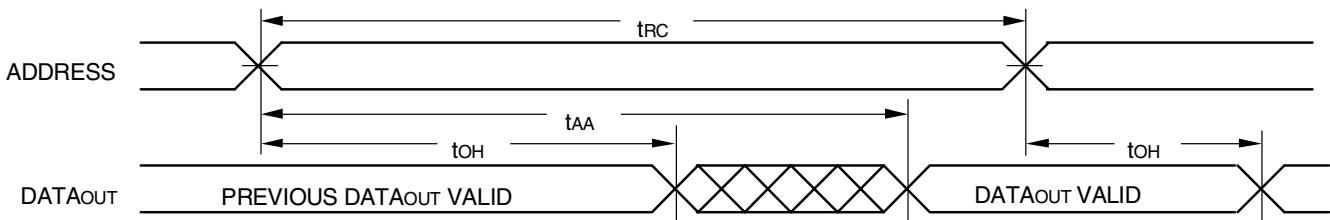
Symbol	Parameter	71016S12		71016S15		71016S20		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
<b>READ CYCLE</b>								
t <sub>RC</sub>	Read Cycle Time	12	—	15	—	20	—	ns
t <sub>AA</sub>	Address Access Time	—	12	—	15	—	20	ns
t <sub>ACS</sub>	Chip Select Access Time	—	12	—	15	—	20	ns
t <sub>CLZ</sub> <sup>(1)</sup>	Chip Select Low to Output in Low-Z	4	—	5	—	5	—	ns
t <sub>CHZ</sub> <sup>(1)</sup>	Chip Select High to Output in High-Z	—	6	—	6	—	8	ns
t <sub>OE</sub>	Output Enable Low to Output Valid	—	7	—	8	—	10	ns
t <sub>OLZ</sub> <sup>(1)</sup>	Output Enable Low to Output in Low-Z	0	—	0	—	0	—	ns
t <sub>OHZ</sub> <sup>(1)</sup>	Output Enable High to Output in High-Z	—	6	—	6	—	8	ns
t <sub>OH</sub>	Output Hold from Address Change	4	—	4	—	5	—	ns
t <sub>BE</sub>	Byte Enable Low to Output Valid	—	7	—	8	—	10	ns
t <sub>BLZ</sub> <sup>(1)</sup>	Byte Enable Low to Output in Low-Z	0	—	0	—	0	—	ns
t <sub>BHZ</sub> <sup>(1)</sup>	Byte Enable High to Output in High-Z	—	6	—	6	—	8	ns
<b>WRITE CYCLE</b>								
t <sub>WC</sub>	Write Cycle Time	12	—	15	—	20	—	ns
t <sub>AW</sub>	Address Valid to End of Write	9	—	10	—	12	—	ns
t <sub>CW</sub>	Chip Select Low to End of Write	9	—	10	—	12	—	ns
t <sub>BW</sub>	Byte Enable Low to End of Write	9	—	10	—	12	—	ns
t <sub>AS</sub>	Address Set-up Time	0	—	0	—	0	—	ns
t <sub>WR</sub>	Address Hold from End of Write	0	—	0	—	0	—	ns
t <sub>WP</sub>	Write Pulse Width	9	—	10	—	12	—	ns
t <sub>DW</sub>	Data Valid to End of Write	7	—	8	—	10	—	ns
t <sub>DH</sub>	Data Hold Time	0	—	0	—	0	—	ns
t <sub>OW</sub> <sup>(1)</sup>	Write Enable High to Output in Low-Z	1	—	1	—	1	—	ns
t <sub>WHZ</sub> <sup>(1)</sup>	Write Enable Low to Output in High-Z	—	6	—	6	—	8	ns

3210 tbl 10

NOTE:

1. This parameter is guaranteed with the AC Load (Figure 2) by device characterization, but is not production tested.

Timing Waveform of Read Cycle No. 1<sup>(1,2,3)</sup>

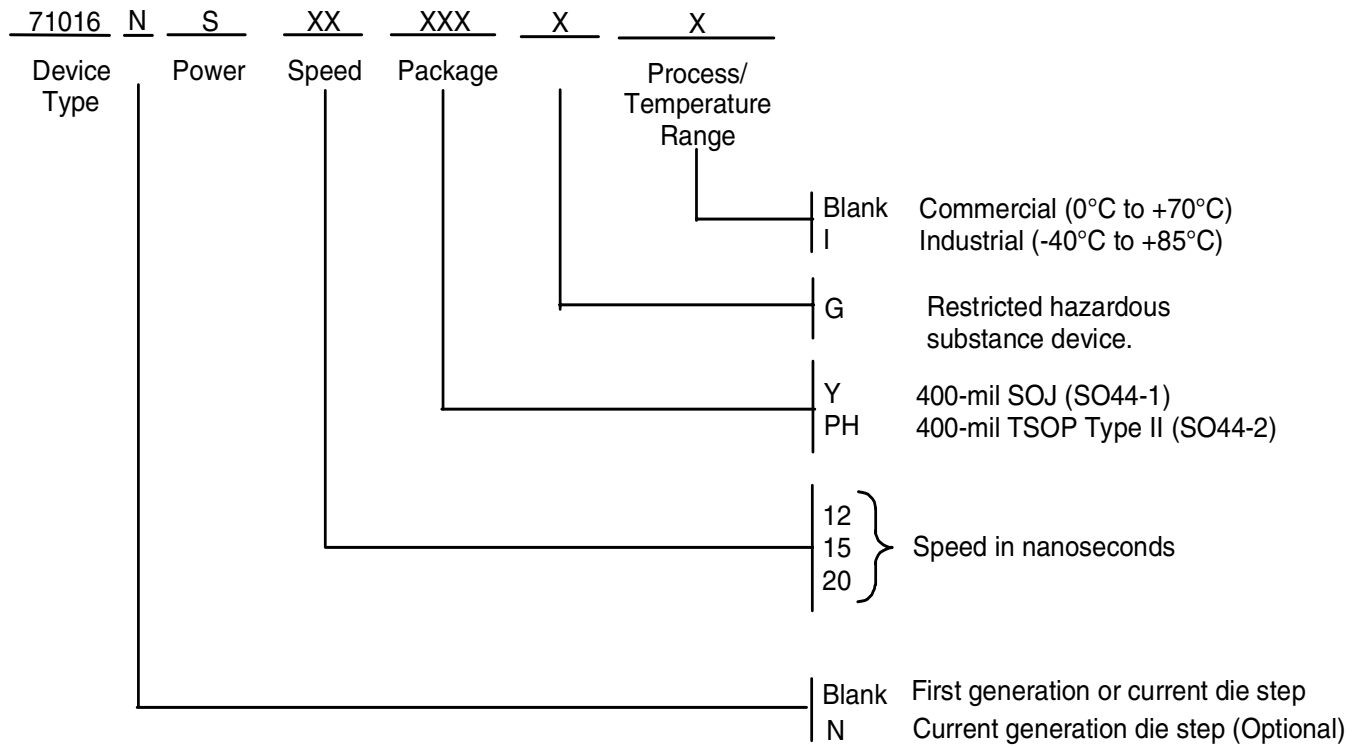


3210 drw 06

NOTES:

1.  $\overline{WE}$  is HIGH for Read Cycle.
2. Device is continuously selected,  $\overline{CS}$  is LOW.
3.  $\overline{OE}$ ,  $\overline{BHE}$ , and  $\overline{BLE}$  are LOW.

### Ordering Information



3210 drw 11